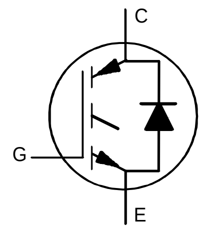
PD - 94773

International
IOR Rectifier

IRG4BC30FD1

Fast CoPack IGBT

INSULATED GATE BIPOLAR TRANSISTOR WITH HYPERFAST DIODE



n-channel

V_{CES} = 600V

$V_{CE(on)\ typ.}$ = 1.59V

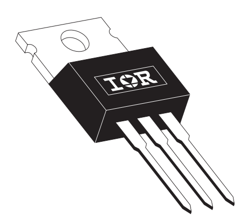
@V_{GE} = 15V, I_C = 17A

Features

- Fast: optimized for medium operating frequencies (1-5 kHz in hard switching, >20kHz in resonant mode).
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than Generation 3.
- IGBT co-packaged with Hyperfast FRED diodes for ultra low recovery characteristics.
- Industry standard TO-220AB package.

Benefits

- Generation 4 IGBT's offer highest efficiency available.
- IGBT's optimized for specific application conditions.
- FRED diodes optimized for performance with IGBT's. Minimized recovery characteristics require less / no snubbing.


TO-220AB

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
I_C @ T_C = 25°C	Continuous Collector Current	31	A
I_C @ T_C = 100°C	Continuous Collector Current	17	
I_{CM}	Pulse Collector Current (Ref.Fig.C.T.5) ①	120	
I_{LM}	Clamped Inductive Load current ②	120	
I_F @ T_C = 100°C	Diode Continuous Forward Current	8	
I_{FM}	Diode Maximum Forward Current	16	
V_{GE}	Gate-to-Emitter Voltage	±20	V
P_D @ T_C = 25°C	Maximum Power Dissipation	100	W
P_D @ T_C = 100°C	Maximum Power Dissipation	42	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Storage Temperature Range, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw	10 lbf·in (1.1 N·m)	

Thermal / Mechanical Characteristics

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case- IGBT	----	----	1.2	°C/W
$R_{\theta JC}$	Junction-to-Case- Diode	----	----	2.0	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	----	0.50	----	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	----	----	80	
Wt	Weight	----	2.0 (0.07)	----	g (oz.)

09/03/03

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage ③	600	—	—	V	V_{GE} = 0V, I_C = 250µA	
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.69	—	V/°C	V_{GE} = 0V, I_C = 1mA	
$V_{CE(on)}$	Collector-to-Emitter Voltage	—	1.59	1.8	V	I_C = 17A	V_{GE} = 15V
		—	1.99	—		I_C = 31A	See Fig. 2, 5
		—	1.7	—		I_C = 17A, T_J = 150°C	
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0	V	V_{CE} = V_{GE}, I_C = 250µA	
$\Delta V_{GE(th)}/\Delta T_J$	Threshold Voltage temp. coefficient	—	-11	—	mV/°C	V_{CE} = V_{GE}, I_C = 250µA	
gfe	Forward Transconductance ④	6.1	10	—	S	V_{CE} = 100V, I_C = 17A	
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	µA	V_{GE} = 0V, V_{CE} = 600V	
		—	—	2500		V_{GE} = 0V, V_{CE} = 600V, T_J = 150°C	
V_{FM}	Diode Forward Voltage Drop	—	2.0	2.4	V	I_F = 8.0A	See Fig. 13
		—	1.3	1.8		I_F = 8.0A, T_J = 150°C	
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ±20V	

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
Q_g	Total Gate Charge (turn-on)	—	57	62	nC	I_C = 17A	
Q_{ge}	Gate-to-Emitter Charge (turn-on)	—	10	12		V_{CC} = 400V See Fig. 8	
Q_{gc}	Gate-to-Collector Charge (turn-on)	—	21	24		V_{GE} = 15V	
$t_{d(on)}$	Turn-On delay time	—	22	—	ns	T_J = 25°C	
t_r	Rise time	—	24	—		I_C = 17A, V_{CC} = 480V	
$t_{d(off)}$	Turn-Off delay time	—	250	320		V_{GE} = 15V, R_G = 23Ω	
t_f	Fall time	—	160	210		Energy losses inlcude "tail" and	
E_{on}	Turn-On Switching Loss	—	370	—	µJ	diode reverse recovery.	
E_{off}	Turn-Off Switching Loss	—	1420	—		See Fig. 9, 10, 11, 18	
E_{ts}	Total Switching Loss	—	1800	2290			
$t_{d(on)}$	Turn-On delay time	—	21	—	ns	T_J = 150°C See Fig. 9,10,11,18	
t_r	Rise time	—	25	—		I_C = 17A, V_{CC} = 480V	
$t_{d(off)}$	Turn-Off delay time	—	400	—		V_{GE} = 15V, R_G = 23Ω	
t_f	Fall time	—	340	—		Energy losses inlcude "tail" and	
E_{ts}	Total Switching Loss	—	3280	—	µJ	diode reverse recovery.	
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package	
C_{ies}	Input Capacitance	—	1170	—	pF	V_{GE} = 0V	
C_{oes}	Output Capacitance	—	100	—		V_{CC} = 30V See Fig. 7	
C_{res}	Reverse Transfer Capacitance	—	11	—		f = 1.0MHz	
t_{rr}	Diode Reverse Recovery Time	—	46	61	ns	T_J = 25°C See Fig.	
		—	85	93		T_J = 125°C 14	I_F = 12A
I_{rr}	Diode Peak Reverse Recovery Current	—	4.8	6.5	A	T_J = 25°C See Fig.	
		—	8.5	10		T_J = 125°C 15	V_R = 200V
Q_{rr}	Diode Reverse Recovery Charge	—	110	190	nC	T_J = 25°C See Fig.	
			410	550		T_J = 125°C 16	di/dt 200A/µs
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During t_b	—	260	—	A/µs	T_J = 25°C See Fig.	
		—	270	—		T_J = 125°C 17	

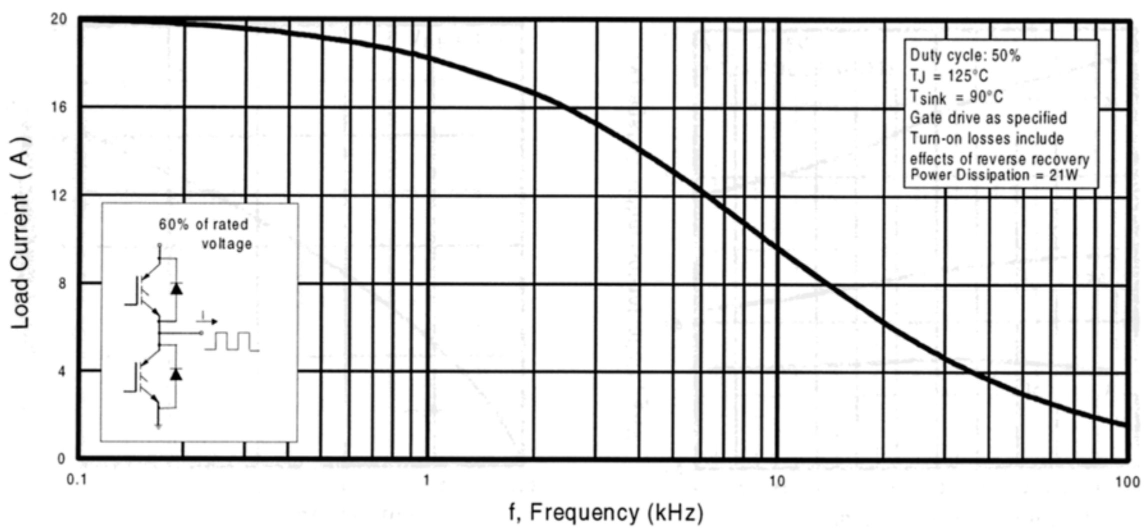


Fig. 1 - Typical Load Current vs. Frequency
(For square wave, $I=I_{RMS}$ of fundamental; for triangular wave, $I=I_{PK}$)

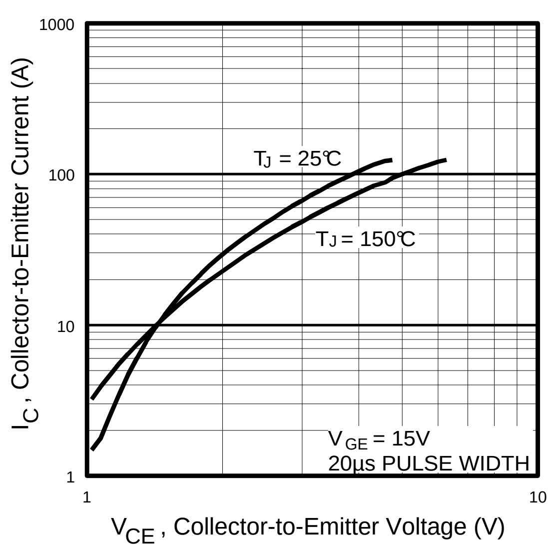


Fig. 2 - Typical Output Characteristics

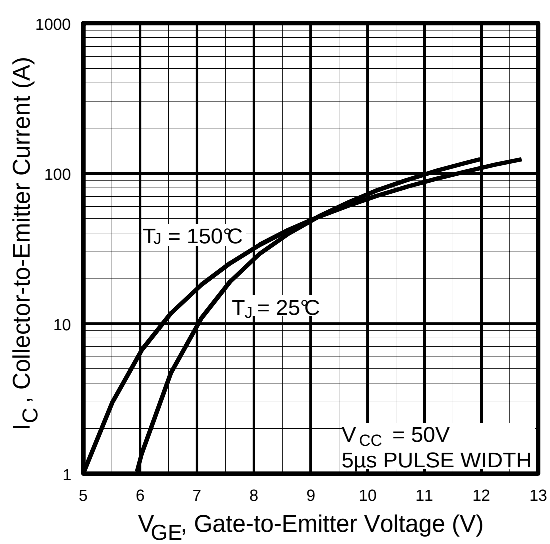


Fig. 3 - Typical Transfer Characteristics

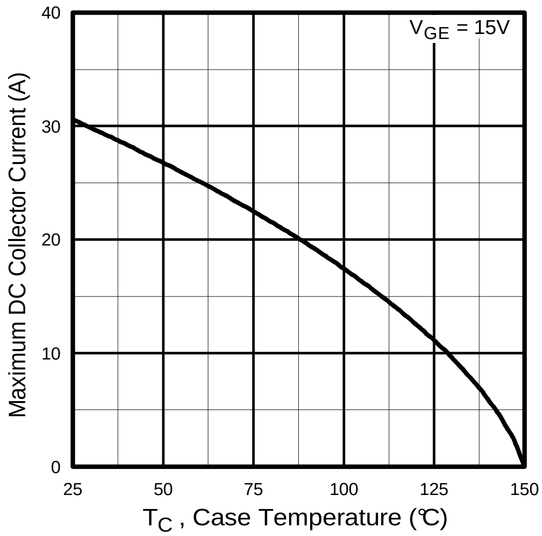


Fig. 4 - Maximum Collector Current vs. Case Temperature

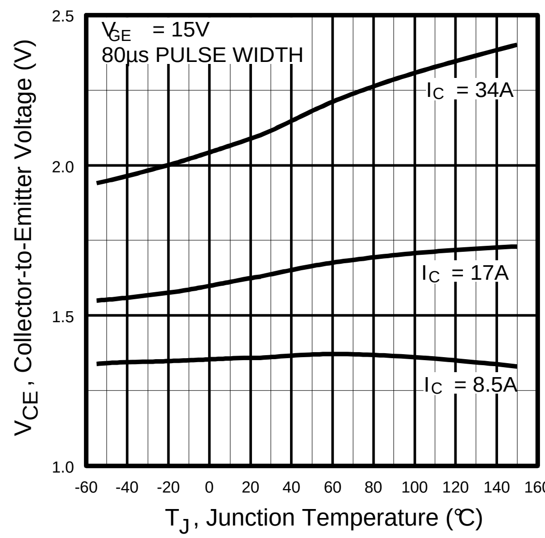


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

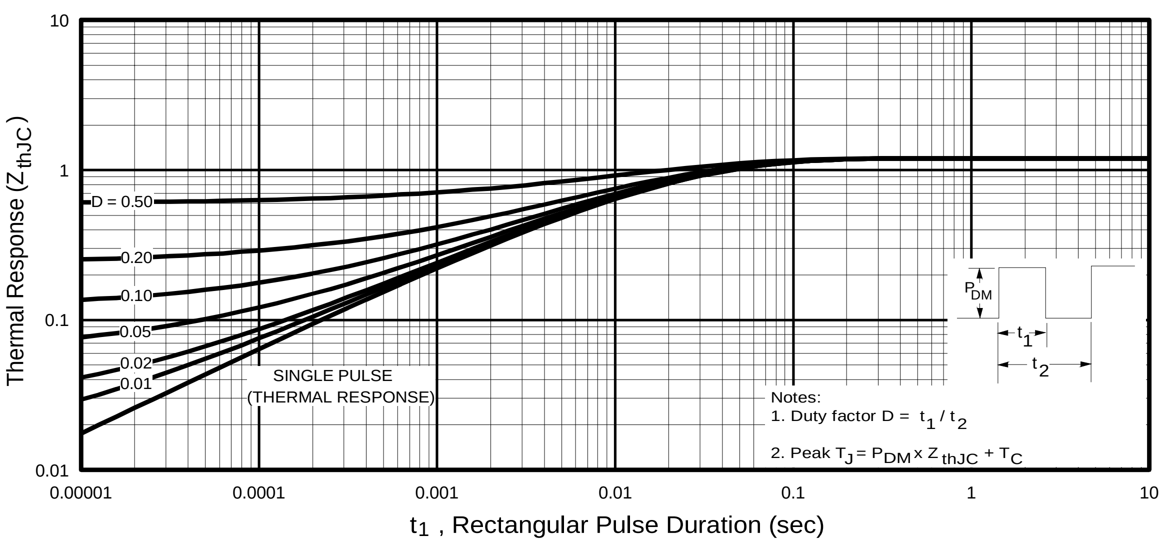


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

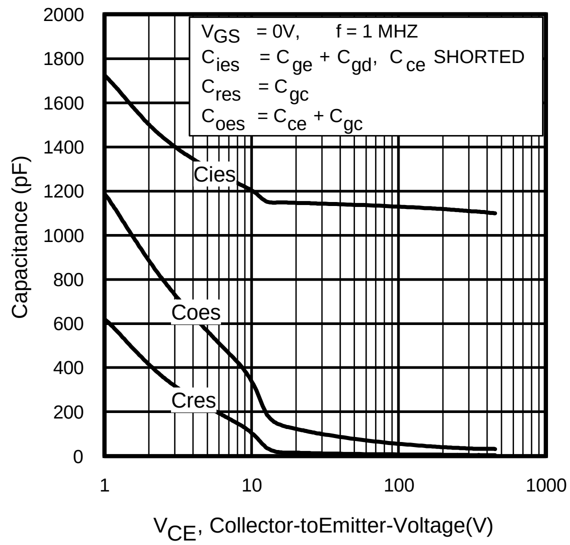


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

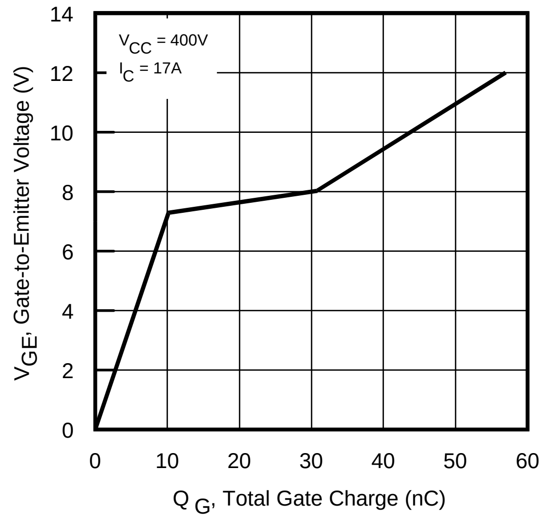


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

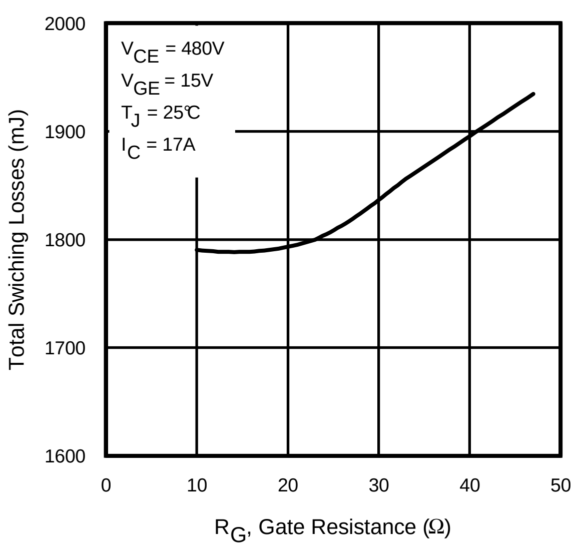


Fig. 9 - Typical Switching Losses vs. Gate Resistance

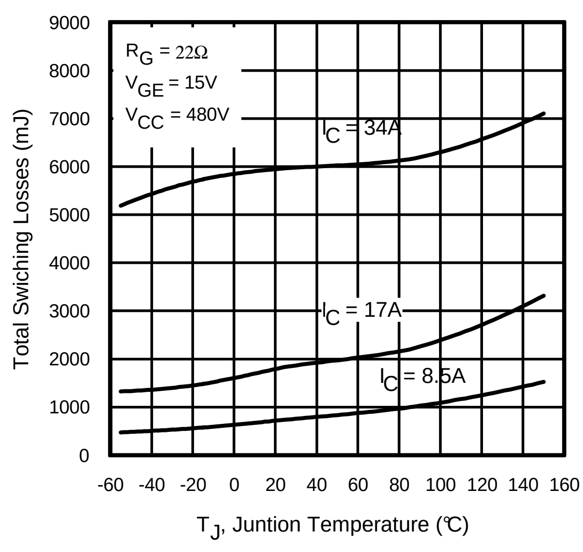


Fig. 10 - Typical Switching Losses vs. Junction Temperature

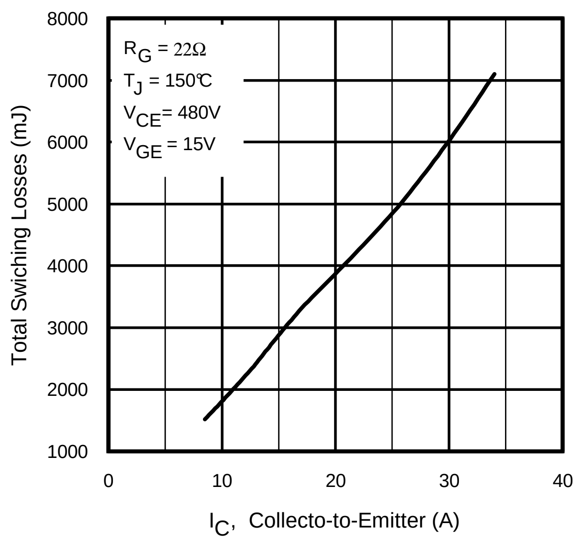


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

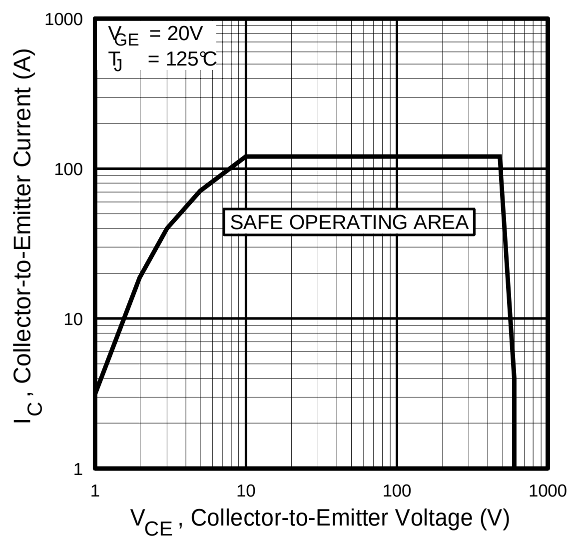


Fig. 12 - Turn-Off SOA

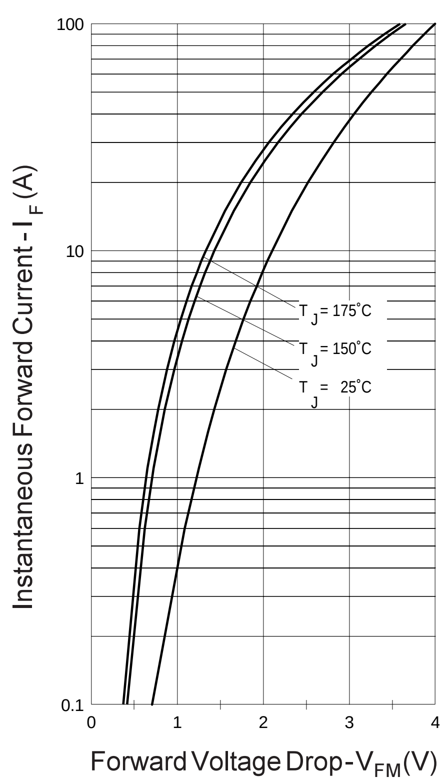


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

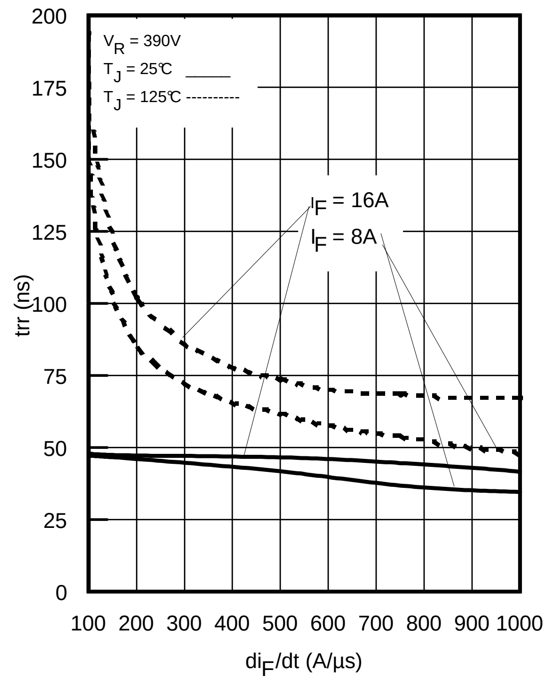


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

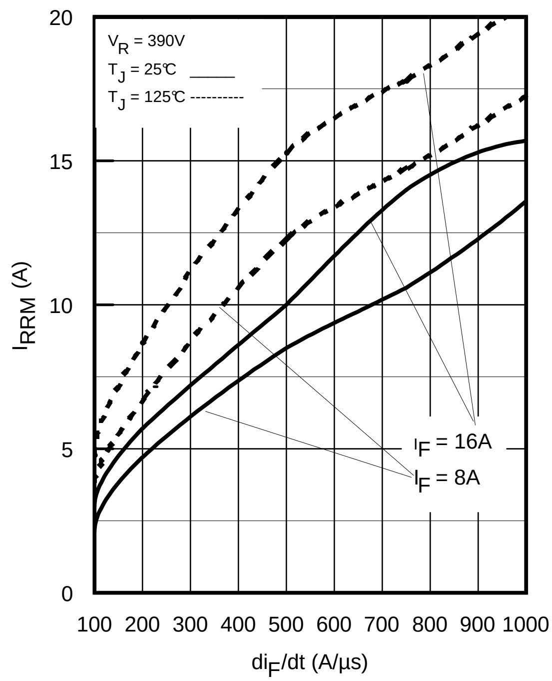


Fig. 15 - Typical Recovery Current vs. di_f/dt

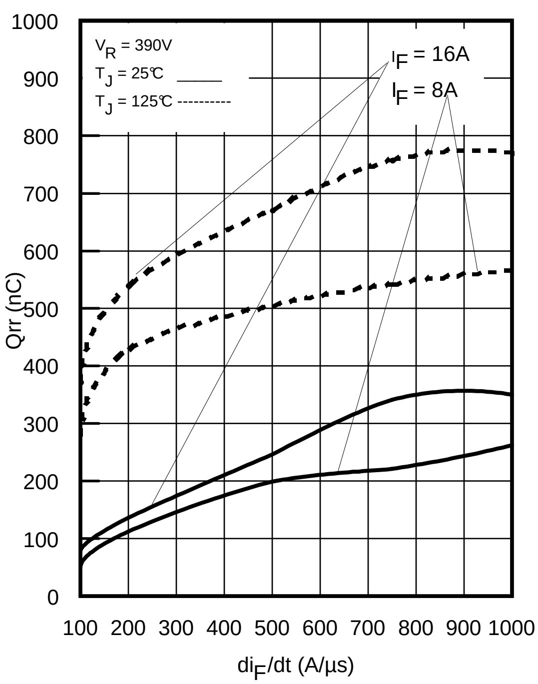


Fig. 16 - Typical Stored Charge vs. di_f/dt

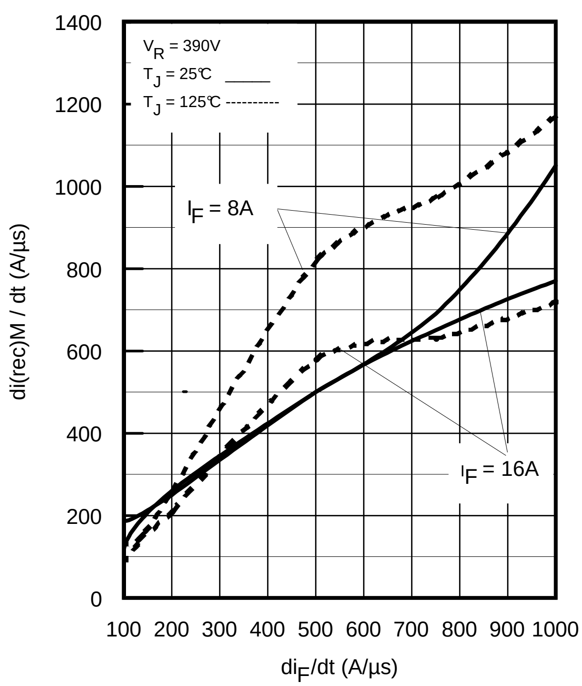


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

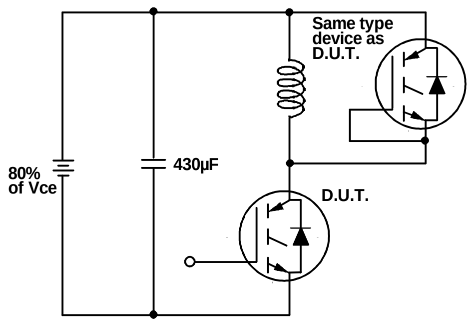


Fig. 18a - Test Circuit for Measurement of I_{LM}, E_{on}, $E_{off(diode)}$, t_{rr}, Q_{rr}, I_{rr}, $t_{d(on)}$, t_r, $t_{d(off)}$, t_f

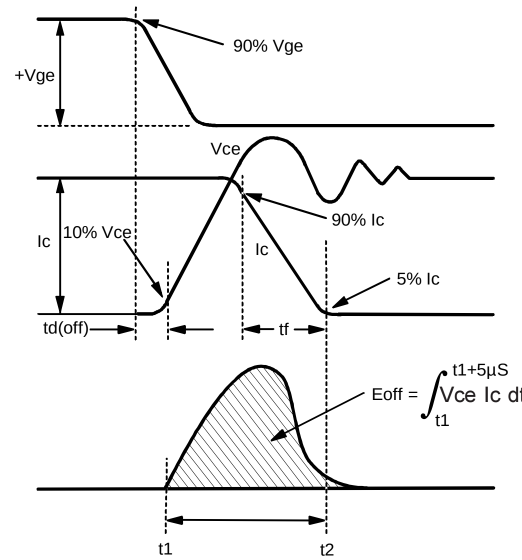


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off}, $t_{d(off)}$, t_f

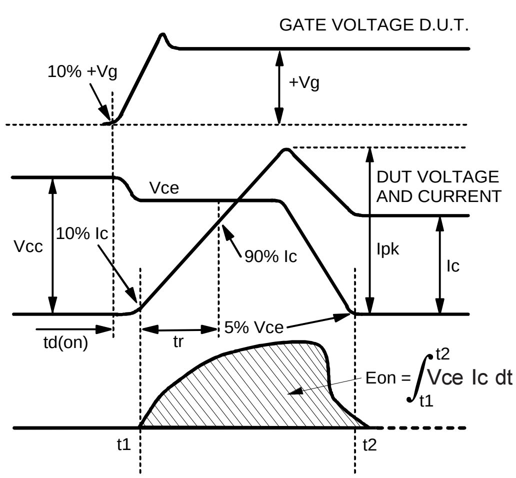


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on}, $t_{d(on)}$, t_r

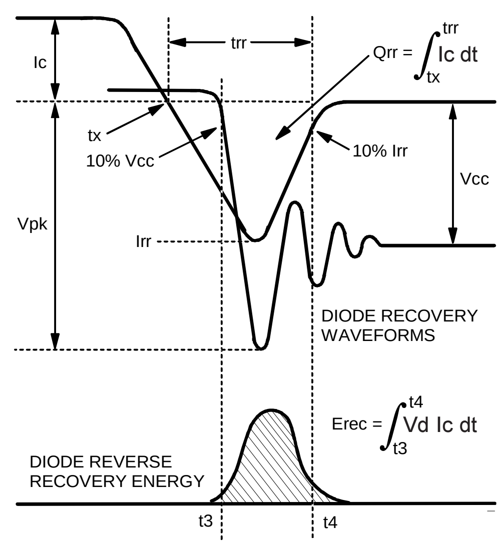


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec}, t_{rr}, Q_{rr}, I_{rr}

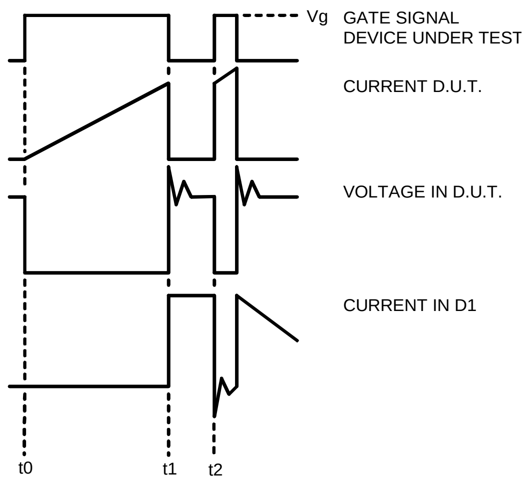


Fig.18e - Macro Waveforms for Figure 18a's Test Circuit

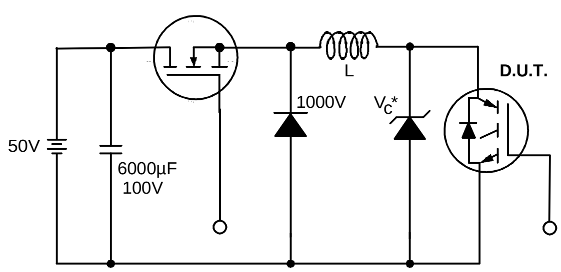


Fig. 19 - Clamped Inductive Load Test Circuit

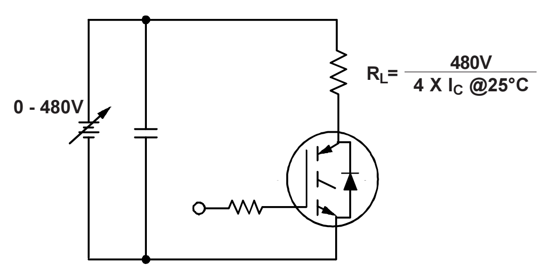
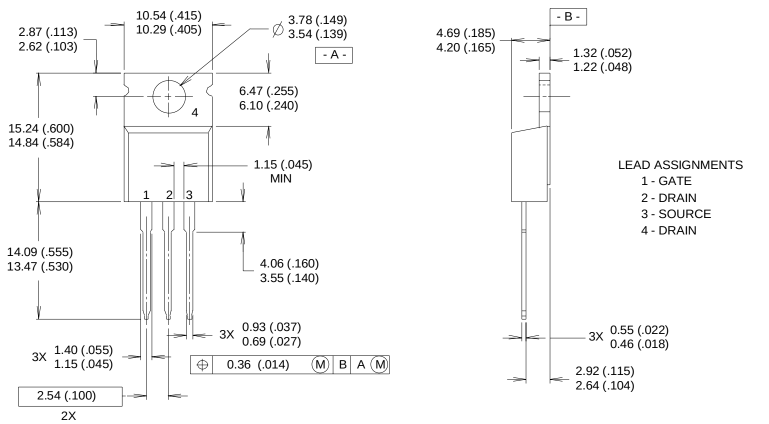


Fig. 20 - Pulsed Collector Current Test Circuit

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.

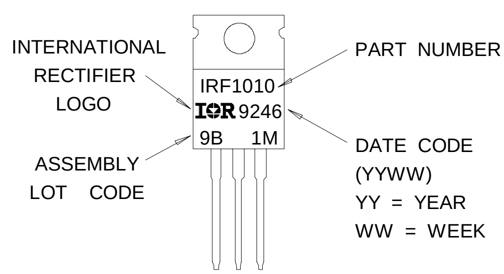
2 CONTROLLING DIMENSION : INCH

3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.

4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

EXAMPLE : THIS IS AN IRF1010
WITH ASSEMBLY
LOT CODE 9B1M



Notes:

① Repetitive rating: V_{GE}=20V; pulse width limited by maximum junction temperature (figure 20).

② V_{CC}=80%(V_{CES}), V_{GE}=20V, L=10µH, R_G = 23Ω (figure 19).

③ Pulse width ≤ 80µs; duty factor ≤ 0.1%.

④ Pulse width 5.0µs, single shot.

⑤ Energy losses include "tail" and diode reverse recovery, using Diode FD100H06A5.

TO-220 package is not recommended for Surface Mount Application.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

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Note: For the most current drawings please refer to the IR website at:
http://www.irf.com/package/